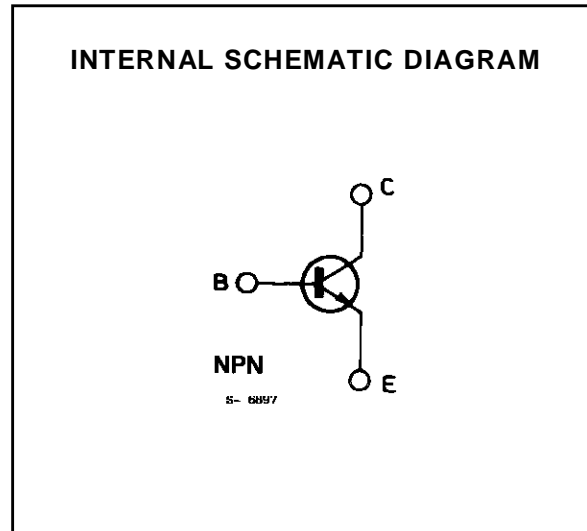
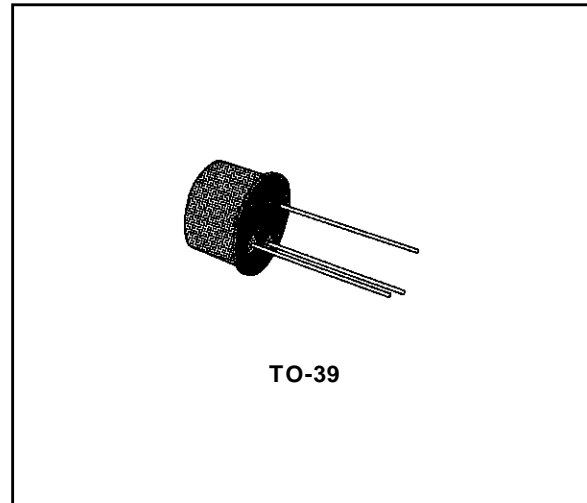


VHF OSCILLATOR POWER AMPLIFIER

DESCRIPTION

The 2N4427 and BFR98 are silicon planar epitaxial NPN transistor in Jedec TO-39 metal case. They are designed for VHF class A, B, or C amplifier and oscillator applications.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-base Voltage ($I_E = 0$)	40	V
V_{CEO}	Collector-emitter Voltage ($I_B = 0$)	20	V
V_{EBO}	Emitter-base Voltage ($I_C = 0$)	3.5	V
I_C	Collector Current	0.5	A
P_{tot}	Total Power Dissipation at $T_{case} \leq 25\text{ }^\circ\text{C}$	3.5	W
T_{stg}, T_j	Storage and Junction Temperature	- 65 to 200	$^\circ\text{C}$

2N4427-BFR98

THERMAL DATA

$R_{th\ j-case}$	Thermal Resistance Junction-case	Max	50	$^{\circ}C/W$
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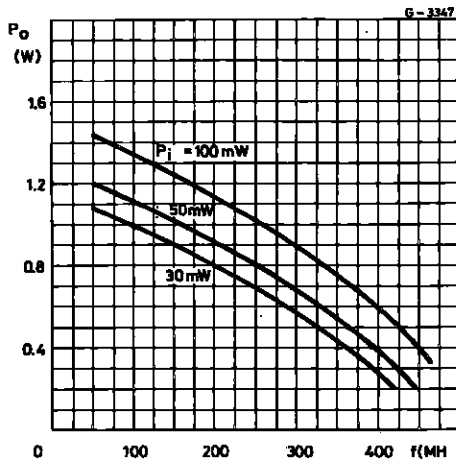
ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CEO}	Collector Cutoff Current ($I_B = 0$)	$V_{CE} = 12\ V$			20	μA
$V_{(BR)CBO}$	Collector-base Breakdown Voltage ($I_E = 0$)	$I_C = 100\ \mu A$	40			V
$V_{CEO(sus)^*}$	Collector-emitter Sustaining Voltage ($I_B = 0$)	$I_C = 5\ mA$	20			V
$V_{CER(sus)^*}$	Collector-Emitter Sustaining Voltage ($R_{BE} = 10\ \Omega$)	$I_C = 5\ mA$	40			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ($I_C = 0$)	$I_E = 100\ \mu A$	3.5			V
$V_{CE(sat)^*}$	Collector-Emitter Saturation Voltage	$I_C = 100\ mA$ $I_B = 20\ mA$			0.5	V
h_{FE}^*	DC Current Gain	$I_C = 100\ mA$ $V_{CE} = 5\ V$ $I_C = 360\ mA$ $V_{CE} = 5\ V$	10 5		200	
f_T	Transition Frequency	$I_C = 50\ mA$ $V_{CE} = 15\ V$ $f = 200\ MHz$	500			MHz
C_{CBO}	Collector-base Capacitance	$I_E = 0$ $V_{CB} = 12\ V$ $f = 1\ MHz$			4	pF
P_o^{**}	Output Power	$V_{CC} = 12\ V$ $P_i = 100\ mW$ $f = 175\ MHz$	1			W
η^{**}	Collector Efficiency	$V_{CC} = 12\ V$ $P_o = 1\ W$ $f = 175\ MHz$	50			%

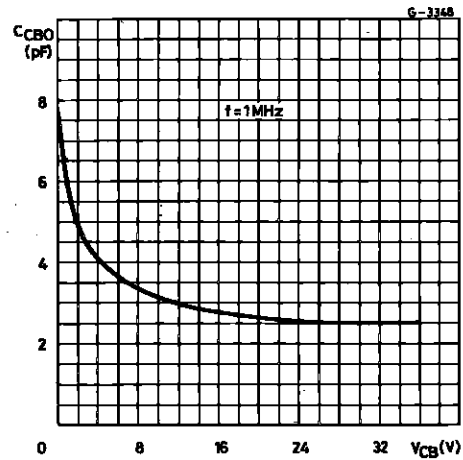
* Pulsed : pulse duration = 300 μs , duty cycle = 1 %.

** See test circuit.

RF Output Power.

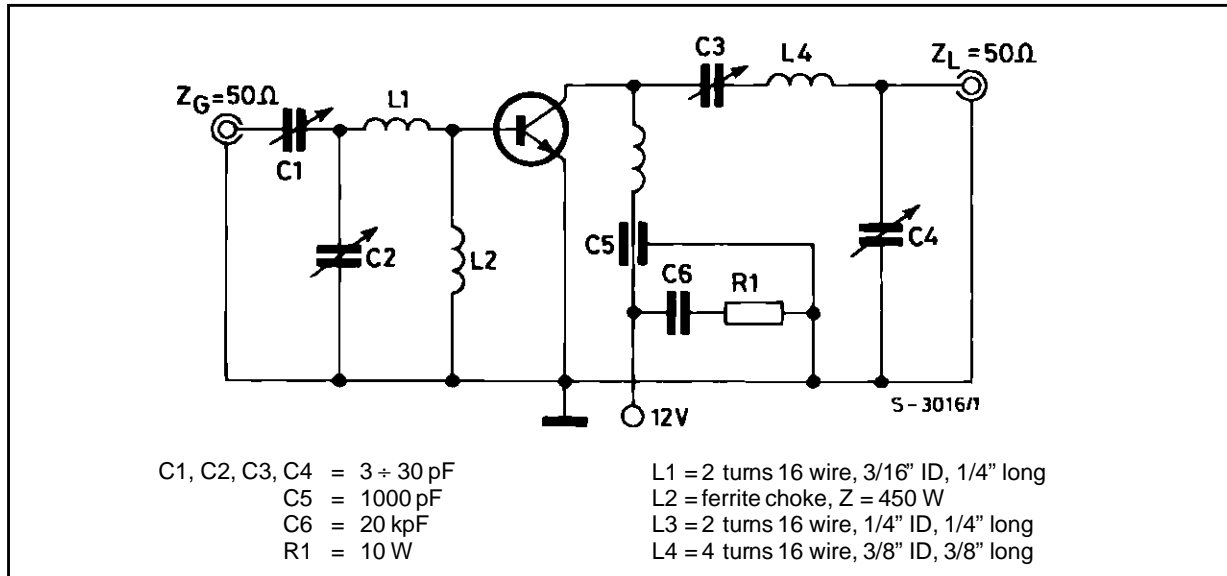


Collector-base Capacitance.



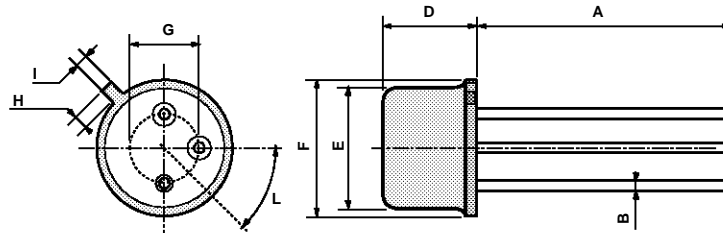
TEST CIRCUIT

Test Circuit for Power Output Measurement ($f = 175 \text{ MHz}$).



TO39 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	12.7			0.500		
B			0.49			0.019
D			6.6			0.260
E			8.5			0.334
F			9.4			0.370
G	5.08			0.200		
H			1.2			0.047
I			0.9			0.035
L	45° (typ.)					



P008B

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